

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions of claims in the application:

Listing of Claims:

1. (Original) A method for modifying a porous film mainly having Si-O bonds, wherein a thermal treatment is conducted without using a metal catalyst by bringing an organic silicon compound including one or more Si-X-Si bond unit (wherein X represents O, NR, C_nH_{2n} , or C_6H_4 ; R represents C_mH_{2m+1} or C_6H_5 ; m is an integer between 1 and 6; and n is 1 or 2) and two or more Si-A bond units (wherein A represents H, OH, OC_eH_{2e+1} or a halogen atom and may be the same or different within a single molecule; and e is an integer between 1 and 6) into contact with the porous film.
2. (Currently Amended) The method for modifying a porous film according to claim 1, wherein the thermal treatment is conducted at a temperature of from 100 to 600 °C.
3. (Currently Amended) The method for modifying a porous film according to claim 1 or 2, wherein the porous film before the treatment is a film having mesopores.
4. (Currently Amended) The method for modifying a porous film according to claim 3, wherein the an average pore diameter of the porous film before the treatment is in a range of 0.5 to 10 nm.

5. (Currently Amended) The method for modifying a porous film according to ~~any one of claims 1 to 4~~ claim 1, wherein the organic silicon compound is a cyclic siloxane.

6. (Currently Amended) A modified porous film obtained by a the method as described in ~~any one of claims 1 to 5~~ claim 1.

7. (Original) A semiconductor material comprising the modified porous film as described in claim 6.

8. (Original) A semiconductor device in which the semiconductor material as described in claim 7 is used.

9. (New) The method for modifying a porous film according to claim 2, wherein the porous film before the treatment is a film having mesopores.

10. (New) The method for modifying a porous film according to claim 2, wherein the organic silicon compound is a cyclic siloxane.

11. (New) The method for modifying a porous film according to claim 3, wherein the organic silicon compound is a cyclic siloxane.

12. (New) The method for modifying a porous film according to claim 4, wherein the organic silicon compound is a cyclic siloxane.

13. (New) The method for modifying a porous film according to claim 9, wherein the organic silicon compound is a cyclic siloxane.
14. (New) A modified porous film obtained by the method as described in claim 2.
15. (New) A modified porous film obtained by the method as described in claim 3.
16. (New) A modified porous film obtained by the method as described in claim 4.
17. (New) A semiconductor material comprising the modified porous film as described in claim 14.
18. (New) A semiconductor material comprising the modified porous film as described in claim 15.
19. (New) A semiconductor device in which the semiconductor material as described in claim 17 is used.
20. (New) A semiconductor device in which the semiconductor material as described in claim 18 is used.